



**THE DATASHEET OF  
NUD3160DMT1G**



# NUD3160, SZNUD3160

## Industrial Inductive Load Driver

This micro-integrated part provides a single component solution to switch inductive loads such as relays, solenoids, and small DC motors without the need of a free-wheeling diode. It accepts logic level inputs, thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

### Features

- Provides Robust Interface between D.C. Relay Coils and Sensitive Logic
- Capable of Driving Relay Coils Rated up to 150 mA at 12 V, 24 V or 48 V
- Replaces 3 or 4 Discrete Components for Lower Cost
- Internal Zener Eliminates Need for Free-Wheeling Diode
- Meets Load Dump and other Automotive Specs
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

### Typical Applications

- Automotive and Industrial Environment
- Drives Window, Latch, Door, and Antenna Relays

### Benefits

- Reduced PCB Space
- Standardized Driver for Wide Range of Relays
- Simplifies Circuit Design and PCB Layout
- Compliance with Automotive Specifications



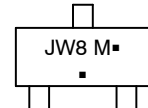
**ON Semiconductor®**

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### MARKING DIAGRAMS



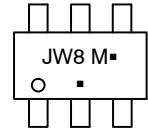
**SOT-23  
CASE 318  
STYLE 21**



JW8 = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)



**SC-74  
CASE 318F  
STYLE 7**

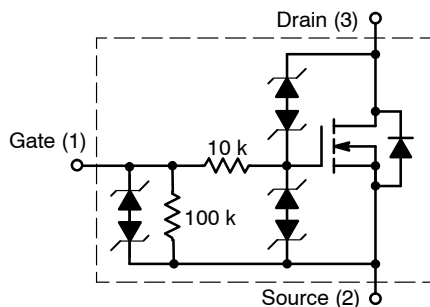


JW8 = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

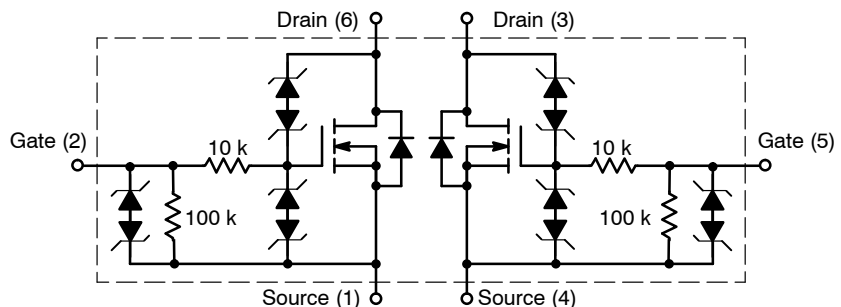
### ORDERING INFORMATION

Device	Package	Shipping†
NUD3160LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SZNUD3160LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NUD3160DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel
SZNUD3160DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.



CASE 318



CASE 318F

**Figure 1. Internal Circuit Diagrams**

## NUD3160, SZNUD3160

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise specified)

Symbol	Rating	Value	Unit
V <sub>DSS</sub>	Drain-to-Source Voltage – Continuous (T <sub>J</sub> = 125°C)	60	V
V <sub>GSS</sub>	Gate-to-Source Voltage – Continuous (T <sub>J</sub> = 125°C)	12	V
I <sub>D</sub>	Drain Current – Continuous (T <sub>J</sub> = 125°C) Minimum copper, double sided board, T <sub>A</sub> = 80°C SOT-23 SC74 Single device driven SC74 Both devices driven 1 in <sup>2</sup> copper, double sided board, T <sub>A</sub> = 25°C SOT-23 SC74 Single device driven SC74 Both devices driven	158 157 132 ea  272 263 230 ea	mA
E <sub>Z</sub>	Single Pulse Drain-to-Source Avalanche Energy (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T <sub>J</sub> Initial = 85°C)	200	mJ
P <sub>PK</sub>	Peak Power Dissipation, Drain-to-Source (Notes 1 and 2) (T <sub>J</sub> Initial = 85°C)	20	W
E <sub>LD1</sub>	Load Dump Pulse, Drain-to-Source (Note 3) R <sub>SOURCE</sub> = 0.5 Ω, T = 300 ms (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T <sub>J</sub> Initial = 85°C)	60	V
E <sub>LD2</sub>	Inductive Switching Transient 1, Drain-to-Source (Waveform: R <sub>SOURCE</sub> = 10 Ω, T = 2.0 ms) (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T <sub>J</sub> Initial = 85°C)	100	V
E <sub>LD3</sub>	Inductive Switching Transient 2, Drain-to-Source (Waveform: R <sub>SOURCE</sub> = 4.0 Ω, T = 50 μs) (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T <sub>J</sub> Initial = 85°C)	300	V
Rev-Bat	Reverse Battery, 10 Minutes (Drain-to-Source) (For Relay's Coils/Inductive Loads of 80 Ω or more)	-14	V
Dual-Volt	Dual Voltage Jump Start, 10 Minutes (Drain-to-Source)	28	V
ESD	Human Body Model (HBM) According to EIA/JESD22/A114 Specification	2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# NUD3160, SZNUD3160

## THERMAL CHARACTERISTICS

Symbol	Rating	Value	Unit	
$T_A$	Operating Ambient Temperature	-40 to 125	°C	
$T_J$	Maximum Junction Temperature	150	°C	
$T_{STG}$	Storage Temperature Range	-65 to 150	°C	
$P_D$	Total Power Dissipation (Note 4) Derating above 25°C	SOT-23	225	mW
			1.8	mW/°C
$P_D$	Total Power Dissipation (Note 4) Derating above 25°C	SC-74	380	mW
			3.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient Minimum Copper	SOT-23	556	°C/W
		SC-74 One Device Powered	556	
		SC-74 Both Devices Equally Powered	398	
	300 mm <sup>2</sup> Copper	SOT-23	395	
		SC-74 One Device Powered	420	
		SC-74 Both Devices Equally Powered	270	

1. Nonrepetitive current square pulse 1.0 ms duration.
2. For different square pulse durations, see Figure 12.
3. Nonrepetitive load dump pulse per Figure 3.
4. Mounted onto minimum pad board.

# NUD3160, SZNUD3160

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Drain to Source Sustaining Voltage (I <sub>D</sub> = 10 mA)	V <sub>BRDSS</sub>	61	66	70	V
Drain to Source Leakage Current (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V) (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125°C) (V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V) (V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125°C)	I <sub>DSS</sub>	–	–	0.5 1.0 50 80	μA
Gate Body Leakage Current (V <sub>GS</sub> = 3.0 V, V <sub>DS</sub> = 0 V) (V <sub>GS</sub> = 3.0 V, V <sub>DS</sub> = 0 V, T <sub>J</sub> = 125°C) (V <sub>GS</sub> = 5.0 V, V <sub>DS</sub> = 0 V) (V <sub>GS</sub> = 5.0 V, V <sub>DS</sub> = 0 V, T <sub>J</sub> = 125°C)	I <sub>GSS</sub>	–	–	60 80 90 110	μA
<b>ON CHARACTERISTICS</b>					
Gate Threshold Voltage (V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 1.0 mA) (V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 1.0 mA, T <sub>J</sub> = 125°C)	V <sub>GS(th)</sub>	1.3 1.3	1.8 –	2.0 2.0	V
Drain to Source On-Resistance (I <sub>D</sub> = 150 mA, V <sub>GS</sub> = 3.0 V) (I <sub>D</sub> = 150 mA, V <sub>GS</sub> = 3.0 V, T <sub>J</sub> = 125°C) (I <sub>D</sub> = 150 mA, V <sub>GS</sub> = 5.0 V) (I <sub>D</sub> = 150 mA, V <sub>GS</sub> = 5.0 V, T <sub>J</sub> = 125°C)	R <sub>DS(on)</sub>	–	–	2.4 3.7 1.8 2.9	Ω
Output Continuous Current (V <sub>DS</sub> = 0.3 V, V <sub>GS</sub> = 5.0 V) (V <sub>DS</sub> = 0.3 V, V <sub>GS</sub> = 5.0 V, T <sub>J</sub> = 125°C)	I <sub>DS(on)</sub>	150 100	200 –	– –	mA
Forward Transconductance (V <sub>DS</sub> = 12 V, I <sub>D</sub> = 150 mA)	g <sub>FS</sub>	–	400	–	mmho
<b>DYNAMIC CHARACTERISTICS</b>					
Input Capacitance (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V, f = 10 kHz)	C <sub>iss</sub>	–	30	–	pf
Output Capacitance (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V, f = 10 kHz)	C <sub>oss</sub>	–	14	–	pf
Transfer Capacitance (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V, f = 10 kHz)	C <sub>rss</sub>	–	6.0	–	pf
<b>SWITCHING CHARACTERISTICS</b>					
Propagation Delay Times: High to Low Propagation Delay; Figure 2, (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 3.0 V) Low to High Propagation Delay; Figure 2, (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 3.0 V)  High to Low Propagation Delay; Figure 2, (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 5.0 V) Low to High Propagation Delay; Figure 2, (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 5.0 V)	t <sub>PHL</sub> t <sub>PLH</sub>  t <sub>PHL</sub> t <sub>PLH</sub>	– –  – –	918 798  331 1160	– –  – –	ns
Transition Times: Fall Time; Figure 2, (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 3.0 V) Rise Time; Figure 2, (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 3.0 V)  Fall Time; Figure 2, (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 5.0 V) Rise Time; Figure 2, (V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 5.0 V)	t <sub>f</sub> t <sub>r</sub>  t <sub>f</sub> t <sub>r</sub>	– –  – –	2290 618  622 600	– –  – –	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# NUD3160, SZNUD3160

## TYPICAL WAVEFORMS

( $T_J = 25^\circ\text{C}$  unless otherwise specified)

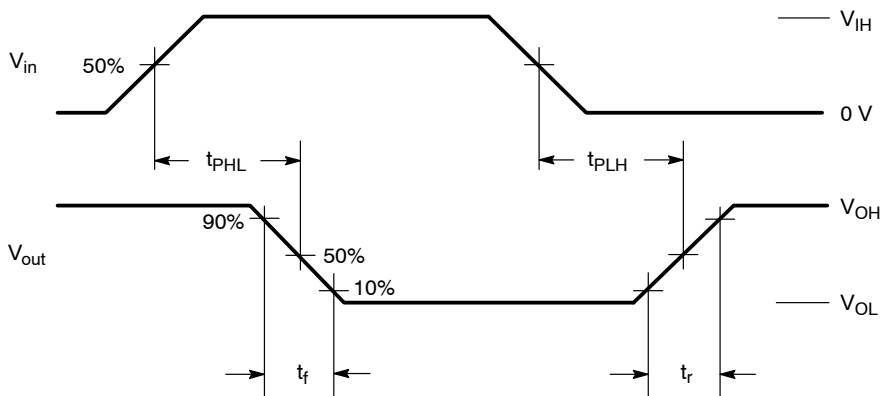


Figure 2. Switching Waveforms

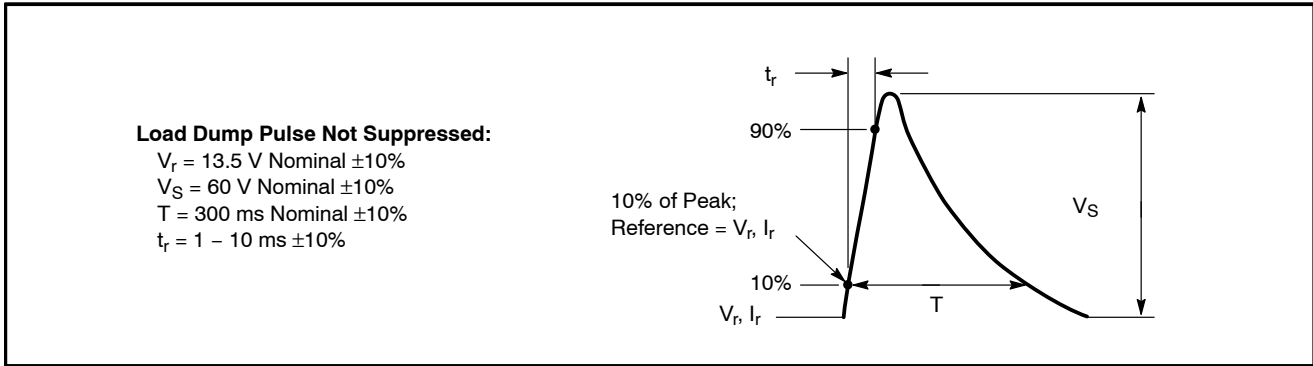
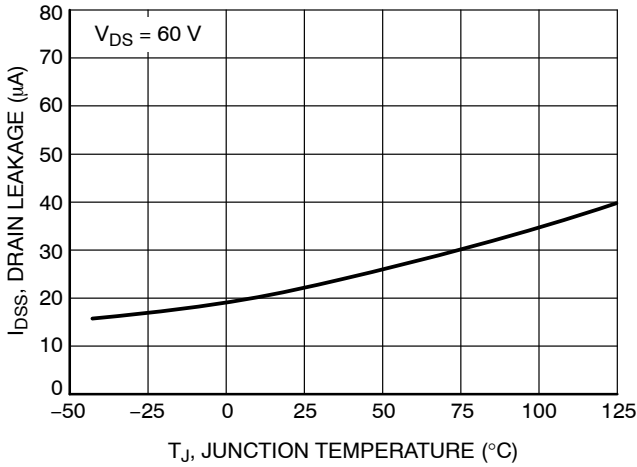


Figure 3. Load Dump Waveform Definition

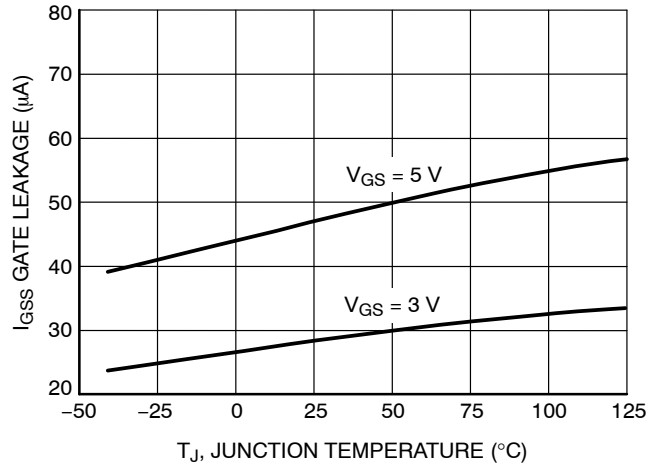
# NUD3160, SZNUD3160

## TYPICAL PERFORMANCE CURVES

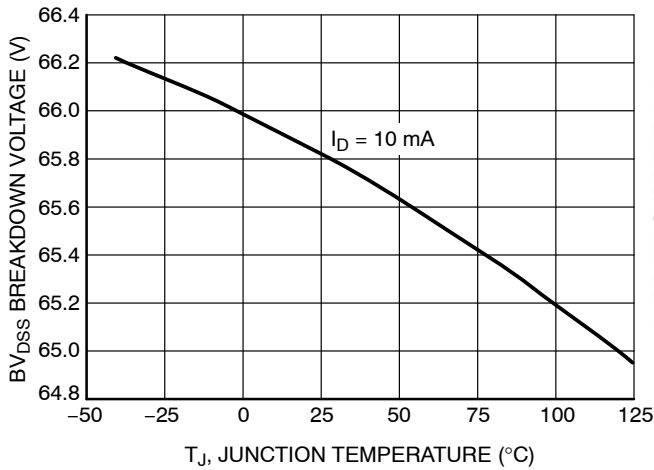
( $T_J = 25^\circ\text{C}$  unless otherwise specified)



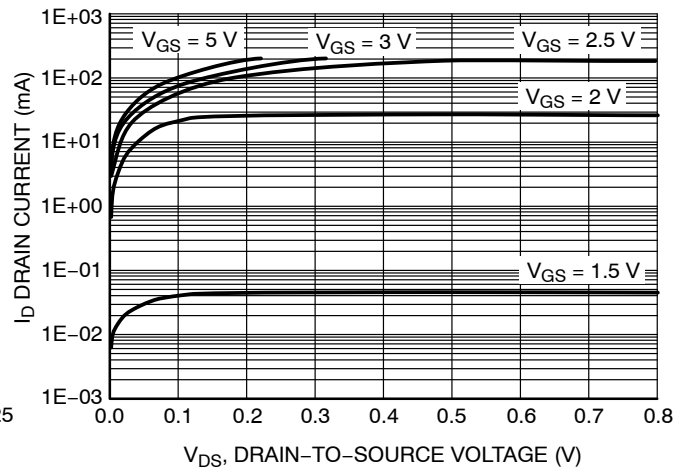
**Figure 4. Drain-to-Source Leakage vs. Junction Temperature**



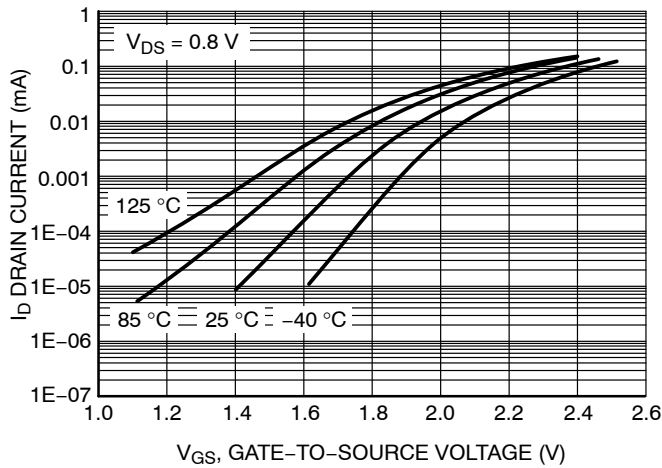
**Figure 5. Gate-to-Source Leakage vs. Junction Temperature**



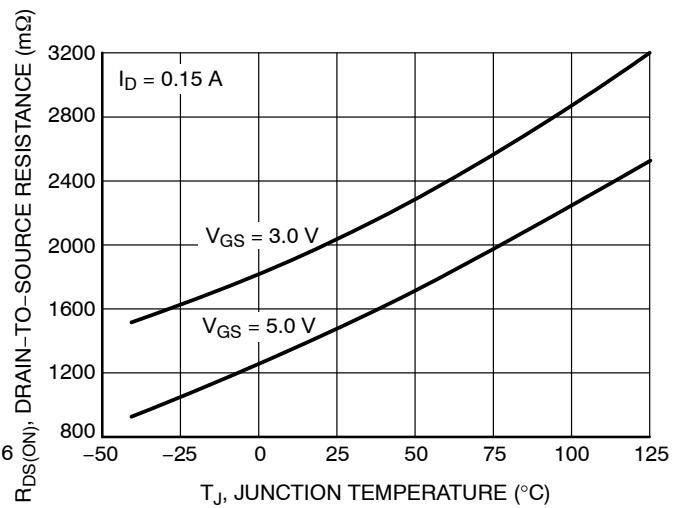
**Figure 6. Breakdown Voltage vs. Junction Temperature**



**Figure 7. Output Characteristics**



**Figure 8. Transfer Function**

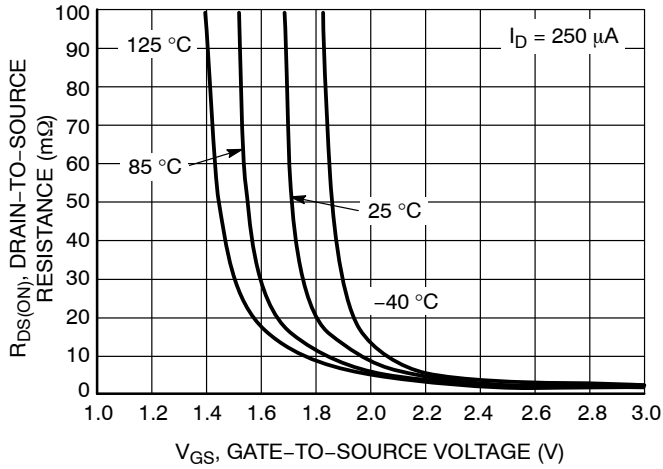


**Figure 9. On Resistance Variation vs. Junction Temperature**

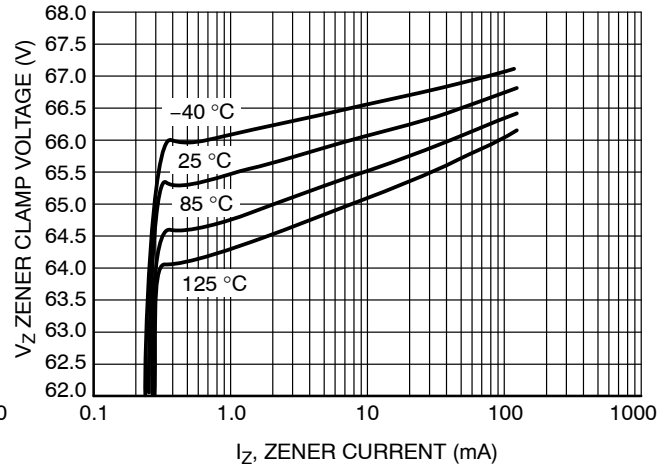
# NUD3160, SZNUD3160

## TYPICAL PERFORMANCE CURVES

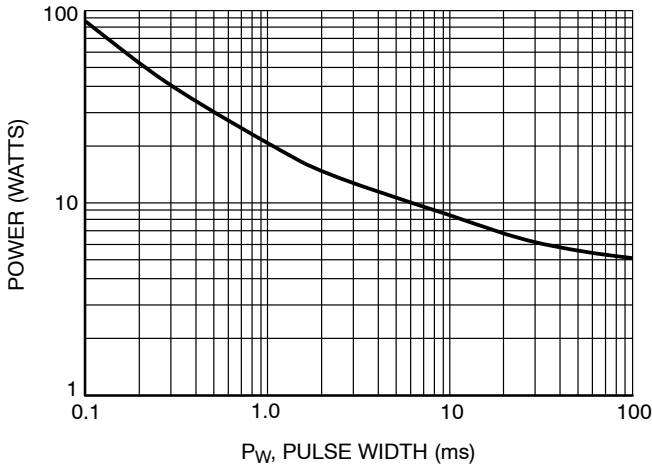
( $T_J = 25^\circ\text{C}$  unless otherwise specified)



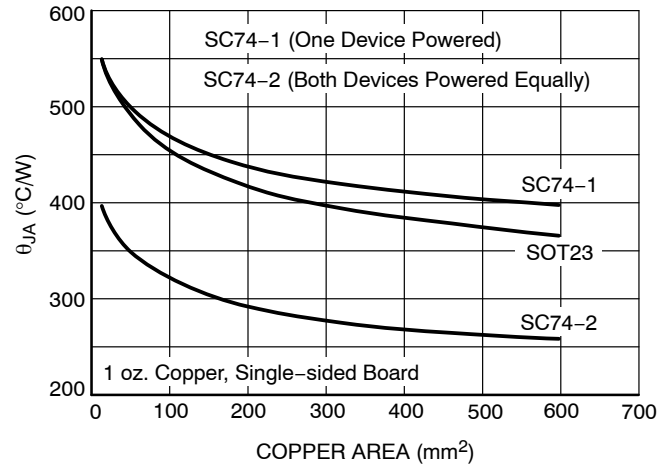
**Figure 10. On Resistance Variation vs. Gate-to-Source Voltage**



**Figure 11. Zener Clamp Voltage vs. Zener Current**



**Figure 12. Maximum Non-repetitive Surge Power vs. Pulse Width**



**Figure 13. Thermal Performance vs. Board Copper Area**

# NUD3160, SZNUD3160

## APPLICATIONS INFORMATION

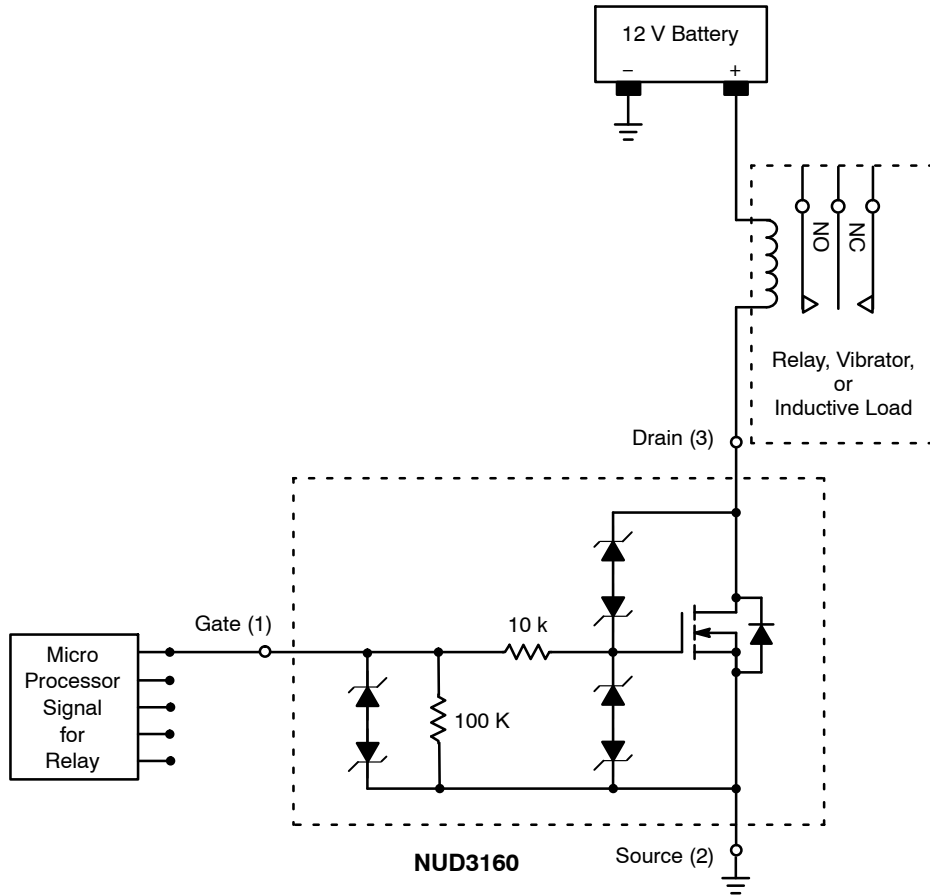
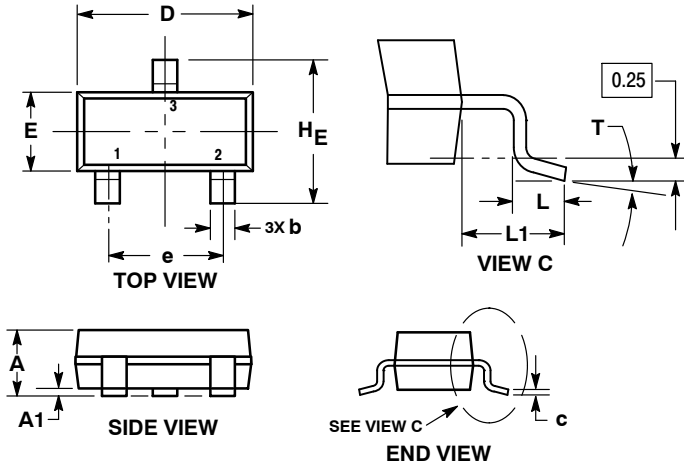


Figure 14. Applications Diagram

# NUD3160, SZNUD3160

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AR



**NOTES:**

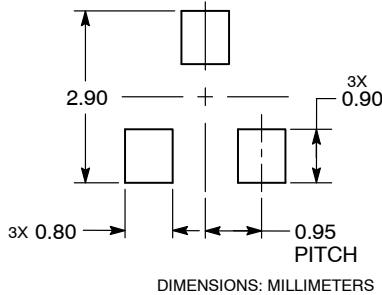
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**STYLE 21:**

- PIN 1. GATE
- SOURCE
- DRAIN

### RECOMMENDED SOLDERING FOOTPRINT\*

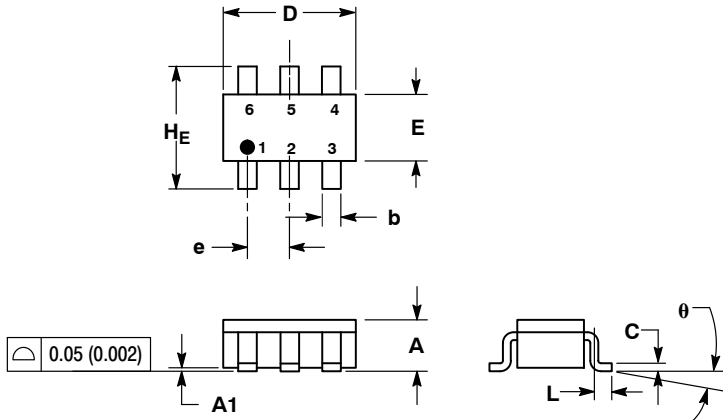


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NUD3160, SZNUD3160

## PACKAGE DIMENSIONS

SC-74  
CASE 318F-05  
ISSUE N

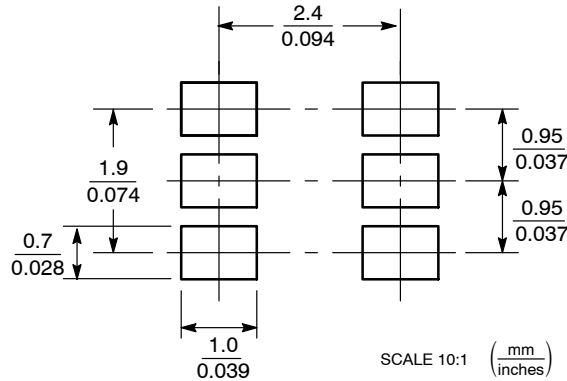


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

- STYLE 7:
- PIN 1. SOURCE 1
  - GATE 1
  - DRAIN 2
  - SOURCE 2
  - GATE 2
  - DRAIN 1

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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